

## 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for thermally demanding environments due to 175 °C rating
- Suitable for logic level gate drive sources

### 1.3 Applications

- DC motor control
- General purpose power switching
- DC-to-DC convertors

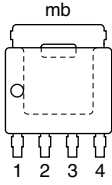
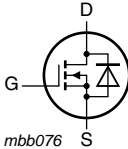
### 1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	75	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 3</a>	-	-	30	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	75	W
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 5\text{ V}$ ; $I_D = 25\text{ A}$ ; $V_{DS} = 60\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 11</a>	-	9	-	nC
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	-	23	28	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <b>SOT669 (LFAK)</b>	 <i>mbb076</i>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PH3075L	LFAK	plastic single-ended surface-mounted package (LFAK); 4 leads	SOT669

## 4. Limiting values

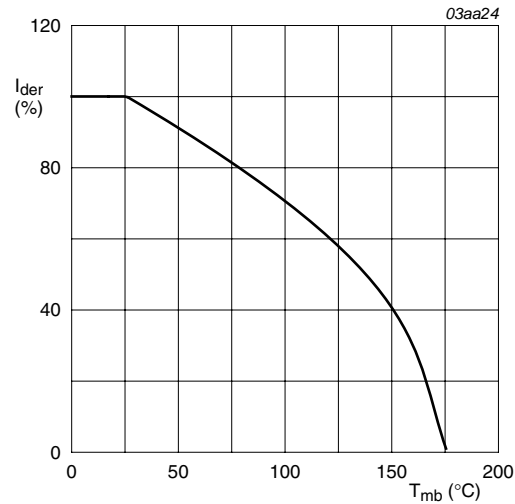
**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$ ; $T_j \leq 175\text{ }^{\circ}\text{C}$	-	75	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$ ; $T_j \leq 175\text{ }^{\circ}\text{C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	75	V
$V_{GS}$	gate-source voltage		-15	15	V
$I_D$	drain current	$V_{GS} = 5\text{ V}$ ; $T_{mb} = 100\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 1</a>	-	21	A
		$V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 3</a>	-	30	A
$I_{DM}$	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 3</a>	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 2</a>	-	75	W
$T_{stg}$	storage temperature		-55	175	$^{\circ}\text{C}$
$T_j$	junction temperature		-55	175	$^{\circ}\text{C}$
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$	-	30	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ }^{\circ}\text{C}$	-	120	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $I_D = 3\text{ A}$ ; $V_{sup} \leq 75\text{ V}$ ; unclamped; $R_{GS} = 50\text{ }\Omega$ ; <a href="#">[1][2]</a>	-	0.89	mJ
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $I_D = 30\text{ A}$ ; $V_{sup} \leq 75\text{ V}$ ; unclamped; $R_{GS} = 50\text{ }\Omega$	-	89	mJ

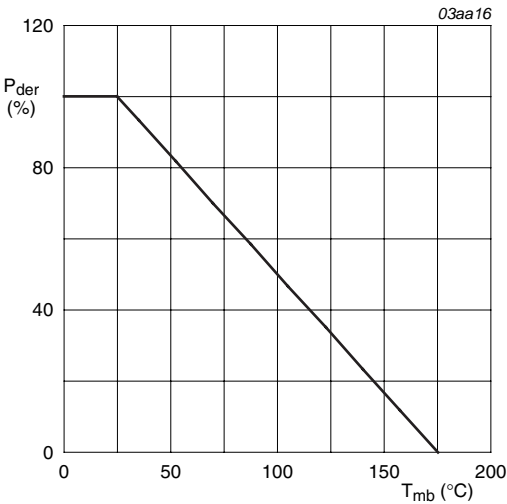
[1] Duty cycle is limited by the maximum junction temperature.

[2] Repetitive avalanche failure is not determined simply by thermal effects. Repetitive avalanche transients should only be applied for short bursts, not every switching cycle.



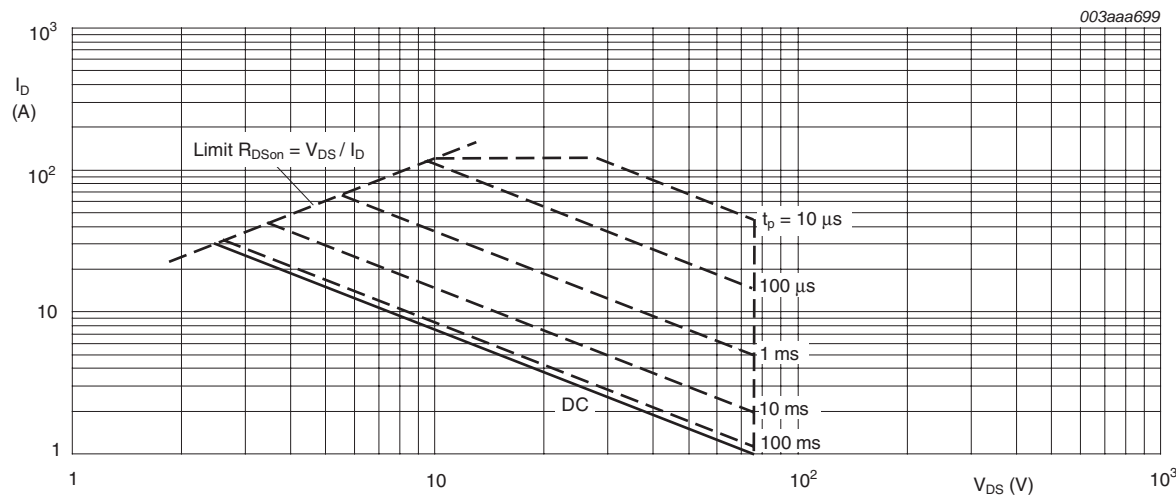
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^{\circ}\text{C}; I_{DM}$  is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	2	K/W

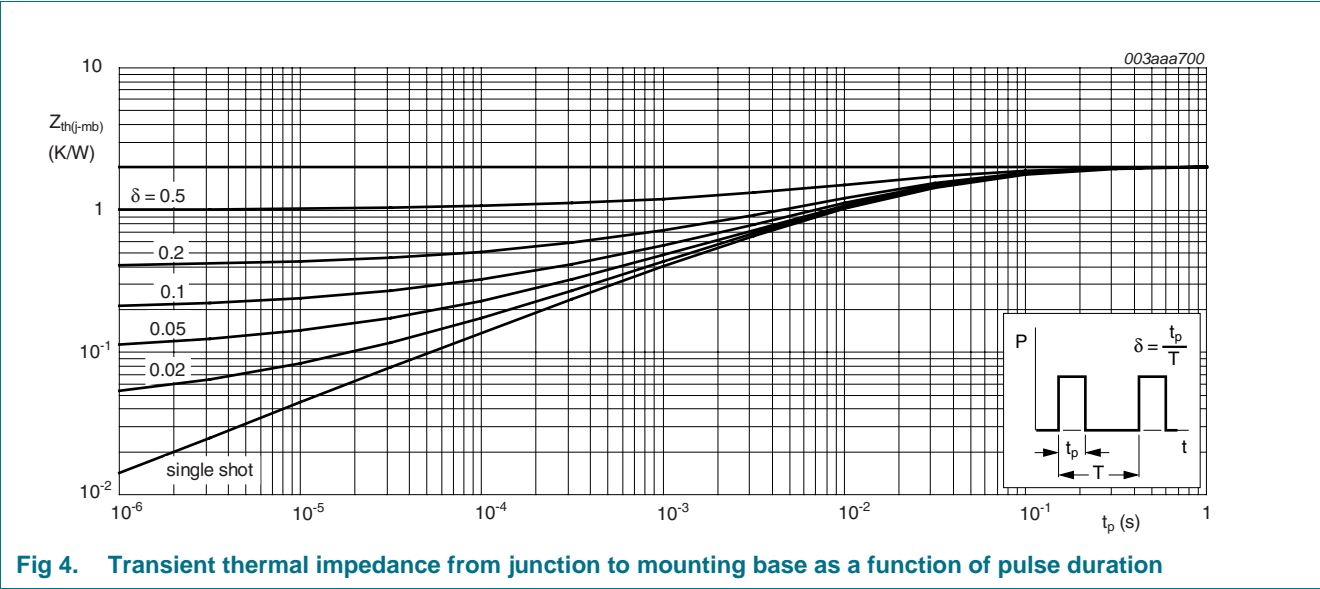


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	70	-	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	75	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <a href="#">Figure 7</a> ; see <a href="#">Figure 8</a>	-	-	2.3	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <a href="#">Figure 7</a> ; see <a href="#">Figure 8</a>	1	1.5	2	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <a href="#">Figure 7</a> ; see <a href="#">Figure 8</a>	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 75 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 75 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 15 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -15 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	-	-	72	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	-	-	34	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	-	23	28	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	-	25	30	mΩ
Dynamic characteristics						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; see <a href="#">Figure 11</a>	-	19	-	nC
Q <sub>GS</sub>	gate-source charge		-	5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see <a href="#">Figure 12</a>	-	1550	2070	pF
C <sub>oss</sub>	output capacitance		-	150	179	pF
C <sub>rss</sub>	reverse transfer capacitance		-	60	80	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C	-	16	-	ns
t <sub>r</sub>	rise time		-	106	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	51	-	ns
t <sub>f</sub>	fall time		-	83	-	ns
Source-drain diode						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <a href="#">Figure 13</a>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	100	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	115	-	nC

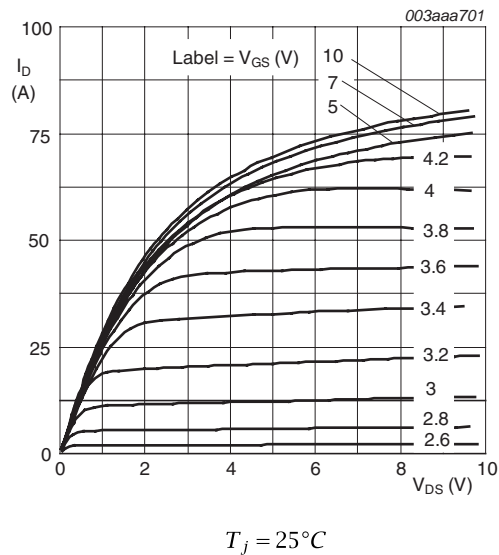


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

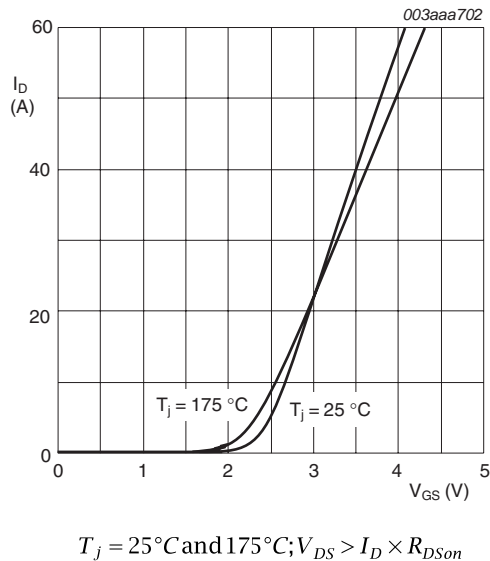


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

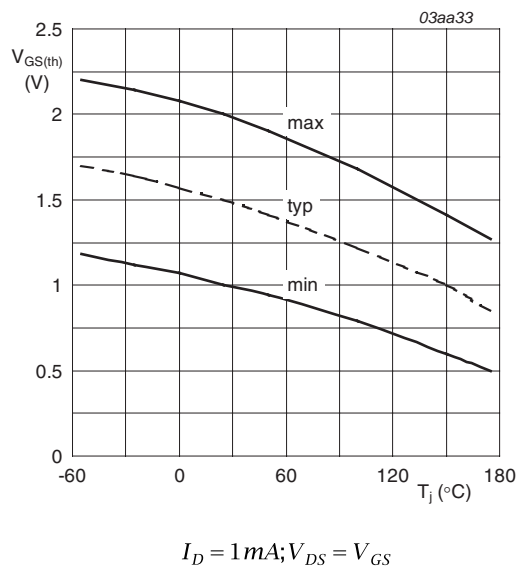


Fig 7. Gate-source threshold voltage as a function of junction temperature

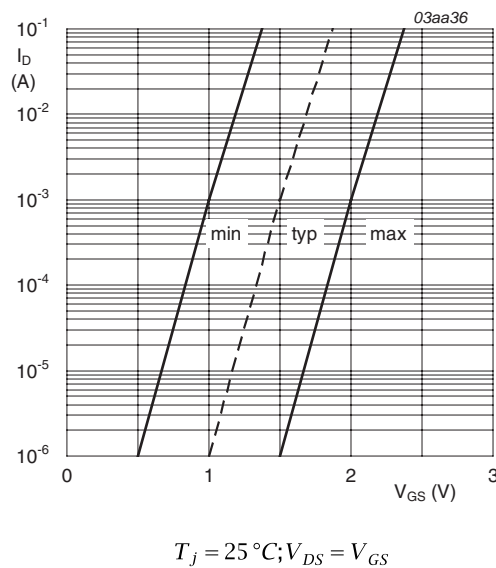


Fig 8. Sub-threshold drain current as a function of gate-source voltage

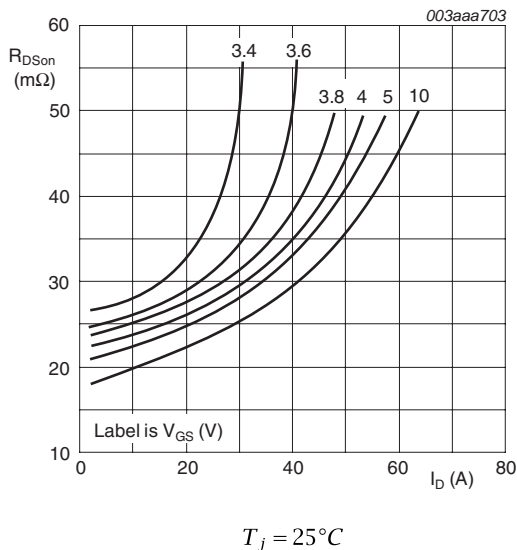
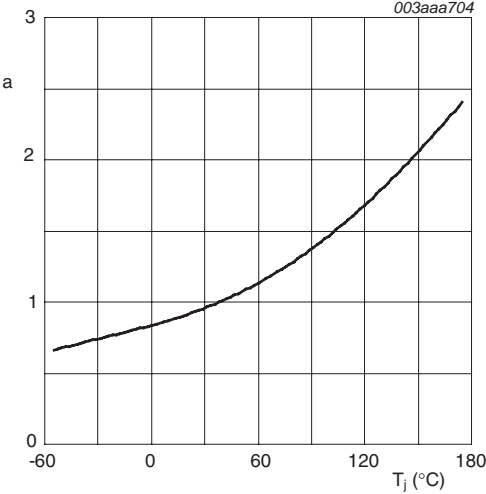


Fig 9. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ C)}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

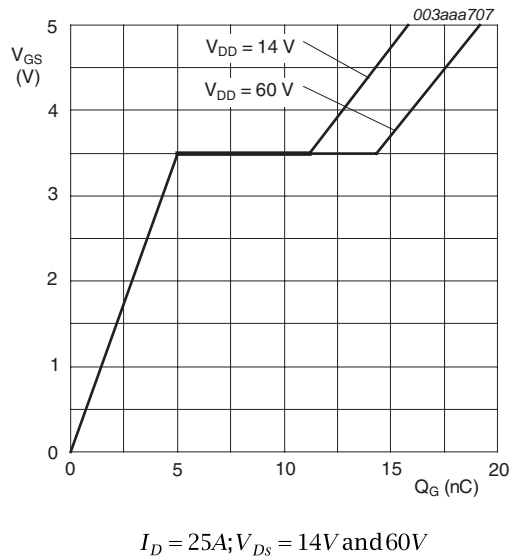


Fig 11. Gate-source voltage as a function of gate charge; typical values

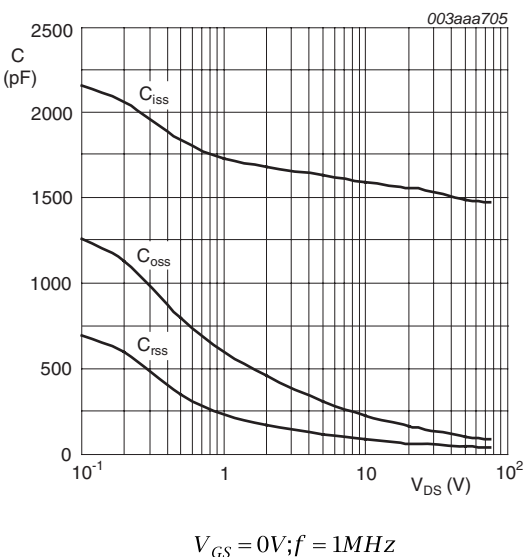
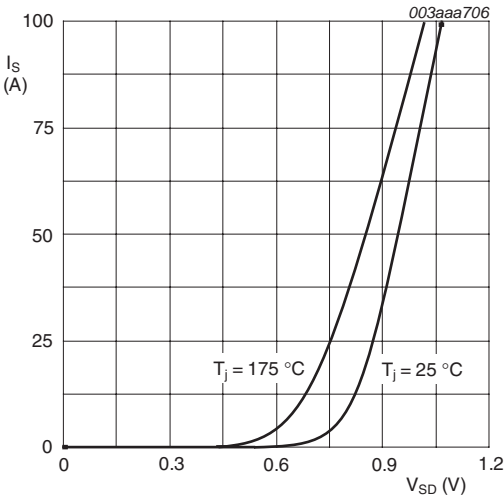


Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





$T_j = 25^\circ\text{C}$  and  $175^\circ\text{C}$ ;  $V_{GS} = 0\text{V}$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LPAK); 4 leads

SOT669

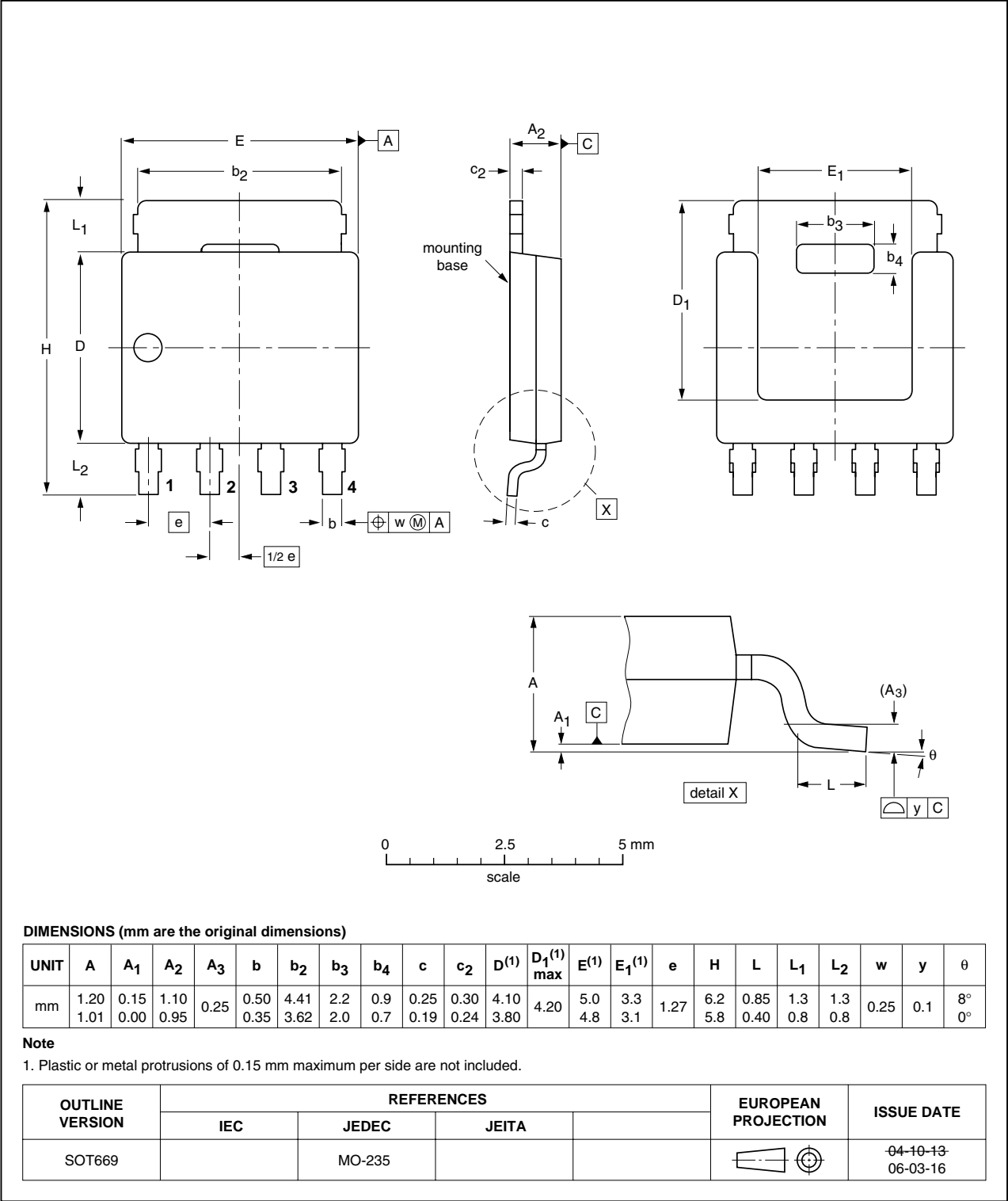


Fig 14. Package outline SOT669 (LPAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PH3075L_2	20090223	Product data sheet	-	PH3075L_1
Modifications:	<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li></ul>			
PH3075L_1 (9397 750 14603)	20050225	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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